

PREFACE

The content of this issue is based on the invited and contributed papers presented by the researchers working in the field of physics and modeling of novel electronic and optoelectronic devices at the International Workshop “Tera- and Nano-Devices: Physics and Modeling” held on October 16–19, 2006 in Aizu-Wakamatsu, Japan. The workshop was organized by V. Ryzhii, G.P. Berman, V. Mitin, T. Otsuji, M. Ryzhii, A. Satou, and M.S. Shur.

The papers in this issue include devices based on carbon nanotubes, generation and detection of terahertz radiation in semiconductor structures including terahertz plasma oscillations and instabilities, terahertz photomixing in semiconductor heterostructures, spin and microwave-induced phenomena in low-dimensional systems, and various computational aspects of device modeling.

We thank the financial support from University of Aizu, Los Alamos National Laboratory, Air Force Office of Scientific Research/Asian Office of Aerospace Research and Development*, University at Buffalo, Sendai Section of the Institute of Electrical and Electronics Engineering, and Technical Group on Terahertz Application Systems of Institute of Electronics, Information, and Communication Engineers.

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